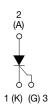


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# Thyristor High Voltage, Phase Control SCR, 12.5 A

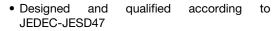




11/10	
-220AB	

PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I <sub>T(AV)</sub>	8 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V			
$V_{TM}$	1.2 V			
I <sub>GT</sub>	15 mA			
TJ	- 40 °C to 125 °C			

#### **FEATURES**





Compliant to RoHS Directive 2002/95/EC

### **APPLICATIONS**

 Typical applications are in input rectification and crowbar (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

#### **DESCRIPTION**

The VS-12TTS08PbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W						

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	UNITS				
I <sub>T(AV)</sub>	Sinusoidal waveform	8	Δ.			
I <sub>T(RMS)</sub>		12.5	A			
V <sub>DRM</sub> /V <sub>RRM</sub>		800	V			
I <sub>TSM</sub>		140	A			
V <sub>T</sub>	8 A, T <sub>J</sub> = 25 °C	1.2	V			
dV/dt		150	V/µs			
dI/dt		100	A/μs			
TJ	Range	- 40 to 125	°C			

VOLTAGE RATINGS							
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA				
VS-12TTS08PbF	800	800	1.0				



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL		TEST CONDITIONS				
Maximum average on-state current	I <sub>T(AV)</sub>	T 100 °C	190° conduction half ains ways	8	^		
Maximum RMS on-state current	I <sub>T(RMS)</sub>	1 <sub>C</sub> = 108 C,	180° conduction, half sine wave	12.5			
Maximum peak, one-cycle,	1	10 ms sine pu	ulse, rated V <sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	120	Α		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pu	ulse, no voltage reapplied, T <sub>J</sub> = 125 °C	140			
Maximum 12t for fusing	l <sup>2</sup> t	10 ms sine pu	ulse, rated V <sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	72	A <sup>2</sup> s		
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pu	ulse, no voltage reapplied, T <sub>J</sub> = 125 °C	100			
Maximum $I^2\sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 1	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C		A²√s		
Maximum on-state voltage drop	$V_{TM}$	8 A, $T_J$ = 25 $^\circ$	8 A, T <sub>J</sub> = 25 °C		V		
On-state slope resistance	r <sub>t</sub>	T 405 00		16.2	mΩ		
Threshold voltage	V <sub>T(TO)</sub>	$T_{\rm J} = 125  ^{\circ}{\rm C}$		0.87	V		
Maximum reverse and direct leakage	1 /1	T <sub>J</sub> = 25 °C	V - Potod V A/	0.05			
current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$		mA		
Typical holding current	l <sub>Η</sub>	Anode supply = 6 V, resistive load, initial I <sub>T</sub> = 1 A		30	IIIA		
Maximum latching current	ال	Anode supply = 6 V, resistive load		50			
Maximum rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 25 °C		150	V/µs		
Maximum rate of rise of turned-on current	dl/dt			100	A/µs		

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P <sub>GM</sub>		8.0	W			
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV			
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α			
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V			
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20	mA			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15				
995		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	1.2				
Maximum required DC gate voltage to trigger	$V_{\mathrm{GT}}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1				
rollage to trigge.		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V			
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detectively	0.2				
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.1	mA			

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8				
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	3	μs			
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	100				



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.5		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque	minimum			6 (5)	kgf · cm	
Mounting torque -	maximum			12 (10)	(lbf · in)	
Marking device Case style TO-220AB 1		12TT	TS08			

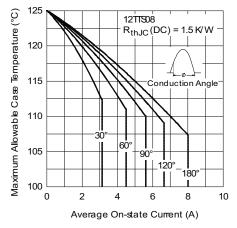


Fig. 1 - Current Ratings Characteristics

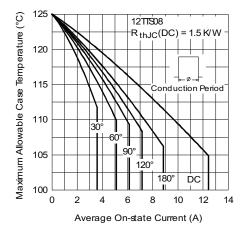


Fig. 2 - Current Ratings Characteristics

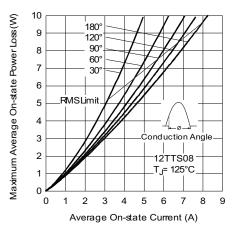


Fig. 3 - On-State Power Loss Characteristics

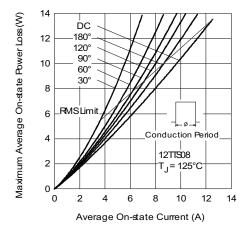


Fig. 4 - On-State Power Loss Characteristics

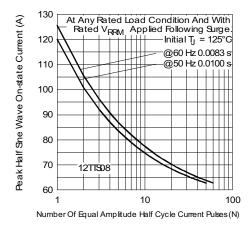


Fig. 5 - Maximum Non-Repetitive Surge Current

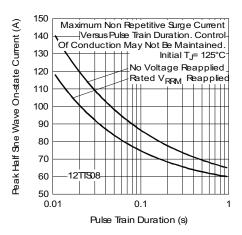


Fig. 6 - Maximum Non-Repetitive Surge Current

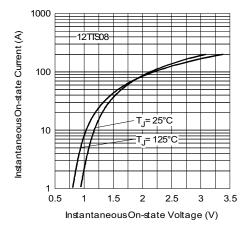


Fig. 7 - On-State Voltage Drop Characteristics

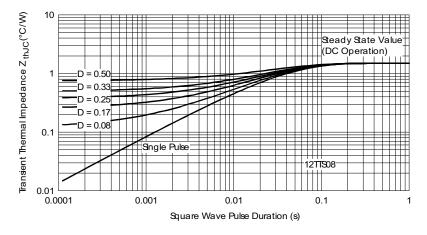
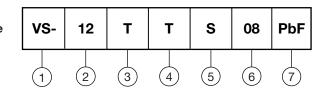


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics



## **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

Current ratings (12 = 12.5 A)

Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220

5 - Type of silicon

S = Standard recovery rectifier

6 - Voltage rating (08 = 800 V)

PbF = Lead (Pb)-free and RoHS compliant

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Part marking information	www.vishay.com/doc?95225				



## **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



## Lead assignments

#### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INC	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS INCHES		NOTES		
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° t	o 93°	
		•	•	•	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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